

## PNP SILICON AMPLIFIER TRANSISTOR

Qualified per MIL-PRF-19500/357

### Devices

2N3634	2N3635	2N3636	2N3637
2N3634L	2N3635L	2N3636L	2N3637L

### Qualified Level

JAN  
JANTX  
JANTXV  
JANS

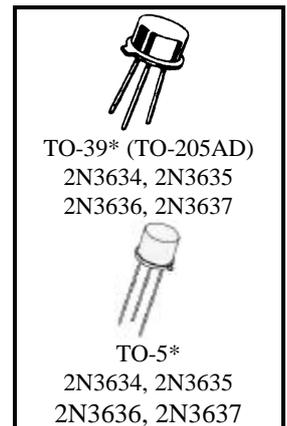
### MAXIMUM RATINGS

Ratings	Symbol	2N3634* 2N3635*	2N3636* 2N3637*	Unit
Collector-Emitter Voltage	$V_{CEO}$	140	175	Vdc
Collector-Base Voltage	$V_{CBO}$	140	175	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0		Vdc
Collector Current	$I_C$	1.0		Adc
Total Power Dissipation	$P_T$	1.0		W
		5.0		W
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200		$^{\circ}C$

\*Electrical characteristics for "L" suffix devices are identical to the "non L" corresponding devices

1) Derate linearly 5.71 mW/ $^{\circ}C$  for  $T_A > +25^{\circ}C$

2) Derate linearly 28.6 mW/ $^{\circ}C$  for  $T_C > +25^{\circ}C$



\*See appendix A for package outline

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Current $I_C = 10$ mAdc	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CEO}$	140 175	Vdc
Collector-Base Cutoff Current $V_{CB} = 100$ Vdc $V_{CB} = 140$ Vdc	2N3634, 2N3635	$I_{CBO}$	100 10	$\eta$ Adc $\mu$ Adc
Emitter-Base Cutoff Current $V_{EB} = 3.0$ Vdc $V_{EB} = 5.0$ Vdc		$I_{EBO}$	50 10	$\eta$ Adc $\mu$ Adc
Collector-Emitter Cutoff Current $V_{CE} = 100$ Vdc		$I_{CEO}$	10	$\mu$ Adc

